NSR1020MW2

20V SOD-323 Schottky Barrier Diode

This Schottky Barrier Diode in the SOD–323 package offers extremely low Vf performance. The low forward voltage makes them capable of handling high current in a very small package. The resulting device is ideally suited for application as a blocking diode in charging applications or as part of discrete buck converter or discrete boost converter. As part of a buck conversion circuit, a boost conversion circuit or a charging circuit the low Vf drop of the Schottky improves the efficiency of the overall device by consuming less power in the forward mode.

Features

- Low Forward Voltage 0.24 Volts (Typ) @ $I_F = 10 \text{ mAdc}$
- High Current Capability
- ESD Rating Human Body Model: CLASS 3B – Machine Model: C
- NSVR Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 125^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	20	Vdc
Peak Revese Voltage	V _{RM}	30	V
Forward Power Dissipation @ T _A = 25°C Derate above 25°C	P _F	200 2.0	mW mW/°C
Forward Current (DC) Continuous	١ _F	1	A
Forward Current t = 8.3 ms Half Sinewave	١ _F	5	A
Repetitive Forward Current period = 1.5 s, Duty Cycle = 66.7%	I _{FRM}	2	A
Junction Temperature	Τ _J	125 Max	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

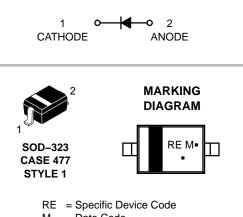
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

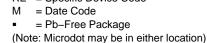


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HIGH CURRENT SCHOTTKY BARRIER DIODE





ORDERING INFORMATION

Device	Package	Shipping†
NSR1020MW2T1G	SOD-323 (Pb-Free)	3000 / Tape & Reel
NSR1020MW2T3G	SOD-323 (Pb-Free)	10,000 / Tape & Reel
NSVR1020MW2T1G	SOD-323 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NSR1020MW2

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Total Capacitance ($V_R = 5.0 \text{ V}, f = 1.0 \text{ MHz}$)	CT	_	25	29	pF
Reverse Leakage (V _R = 15 V)	I _R	-	_	40	μAdc
Forward Voltage (I _F = 1 mAdc)	V _F	_	_	0.20	Vdc
Forward Voltage (I _F = 10 mAdc)	V _F	_	_	0.26	Vdc
Forward Voltage (I _F = 100 mAdc)	V _F	_	_	0.33	Vdc
Forward Voltage (I _F = 500 mAdc)	V _F	_	_	0.44	Vdc
Forward Voltage (I _F = 1000 mAdc)	V _F	_	_	0.54	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

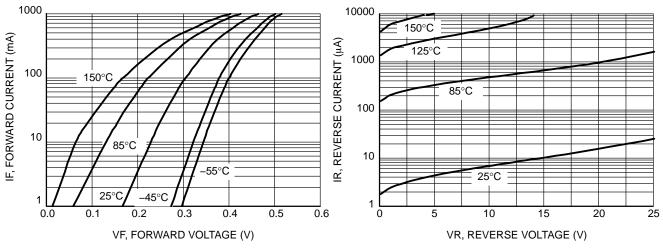


Figure 1. Forward Voltage

Figure 2. Leakage Current

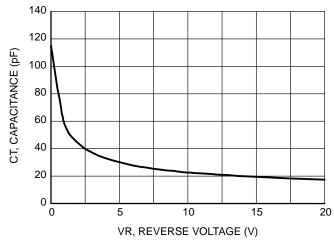
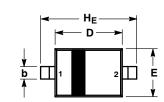


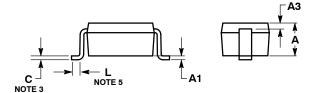
Figure 3. Total Capacitance











SOLDERING FOOTPRINT*



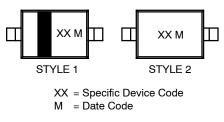
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DATE 13 MAR 2007

- NOTES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETERS.
 LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
 DIMENSION L IS MEASURED FROM END OF RADIUS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15 REF		0.006 REF			
b	0.25	0.32	0.4	0.010	0.012	0.016
С	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
Е	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
HE	2.30	2.50	2.70	0.090	0.098	0.105

GENERIC **MARKING DIAGRAM***



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present.

STYLE 1: PIN 1. CATHODE (POLARITY BAND) 2. ANODE STYLE 2: NO POLARITY

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SOD-323 CASE 477-02

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